

UNIT

V

Ω

nC

N-Channel Power MOSFET

600V, 4.0A, 2.5Ω

FEATURES

- 100% Avalanche Tested
- Pb-free plating •
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition •

APPLICATION

- Power Supply
- Lighting







KEY PERFORMANCE PARAMETERS

VALUE

600

2.5

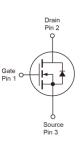
14.5

PARAMETER

 V_{DS}

R_{DS(on)} (max)

Qg



HALOGEN

Notes: MSL 3 (Moisture Sensitivity Level) for TO-252 (D-PAK) per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)						
PARAMETER		SYMBOL	IPAK/DPAK ITO-220		UNIT	
Drain-Source Voltage		V _{DS}	600		V	
Gate-Source Voltage		V_{GS}	±30		V	
Continuous Drain Current (Note 1)	_c = 25°C		4.0		A	
T _c	c= 100°C	I _D	2.4			
Pulsed Drain Current (Note 2)		I _{DM}	16	i	А	
Total Power Dissipation @ T _C = 25°C		P _{DTOT}	50	25	W	
Single Pulsed Avalanche Energy (Note 3)		E _{AS}	70		mJ	
Single Pulsed Avalanche Current (Note 3)		I _{AS}	4		А	
Repetitive Avalanche Energy (Note 2)		E _{AR}	5		mJ	
Peak Diode Recovery (Note 4)		dV/dt	4.5	5	V/ns	
Operating Junction and Storage Temperatur	e Range	T _J , T _{STG}	- 55 to	+150	°C	

THERMAL PERFORMANCE					
PARAMETER	SYMBOL	IPAK/DPAK	ITO-220	UNIT	
Junction to Case Thermal Resistance	R _{ejc}	2.5	5	°C/W	
Junction to Ambient Thermal Resistance	$R_{\Theta JA}$	83	62.5	°C/W	

Notes: ReJA is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. R_{BJC} is guaranteed by design while R_{BCA} is determined by the user's board design. R_{0JA} shown below for single device operation on FR-4 PCB in still air.



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ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	ТҮР	MAX	UNIT
Static (Note 5)						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250 \mu A$	BV _{DSS}	600			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	V _{GS(TH)}	2.5	3.5	4.5	V
Gate Body Leakage	$V_{GS} = \pm 30 \text{V}, V_{DS} = 0 \text{V}$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 600V, V_{GS} = 0V$	I _{DSS}			1	μA
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 2.0A$	R _{DS(on)}		2.2	2.5	Ω
Forward Transfer Conductance	$V_{DS} = 40V, I_{D} = 2A$	g _{fs}		2.6		S
Dynamic ^(Note 6)						
Total Gate Charge		Qg		14.5		
Gate-Source Charge	$V_{DS} = 480V, I_D = 4.0A,$	Q _{gs}		3.4		nC
Gate-Drain Charge	V _{GS} = 10V	Q _{gd}		7		
Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1.0MHz	C _{iss}		500		
Output Capacitance		C _{oss}		53.2		pF
Reverse Transfer Capacitance		C _{rss}		7		
Switching (Note 7)						
Turn-On Delay Time		t _{d(on)}		11		
Turn-On Rise Time	$V_{DD} = 300V,$	t _r		20		
Turn-Off Delay Time	$R_{GEN} = 25\Omega,$ $I_D = 4.0A, V_{GS} = 10V,$	t _{d(off)}		30		ns
Turn-Off Fall Time		t _f		19		
Source-Drain Diode (Note 5)	·					
Forward On Voltage	$I_{\rm S} = 4.0$ A, $V_{\rm GS} = 0$ V	V _{SD}			1.13	V
Reverse Recovery Time	$V_{GS}=0V, I_{S}=2A$	t _{rr}		522		ns
Reverse Recovery Charge	$dI_F/dt = 100A/\mu s$	Q _{rr}		1.6		μC
Source Current	Integral reverse diode	I _S			4	Α
Source Current (Pulse)	in the MOSFET	I _{SM}			16	А

Notes:

- 1. Current limited by package.
- 2. Pulse width limited by the maximum junction temperature.
- 3. L = 8mH, I_{AS} = 4.0A, V_{DD} = 50V, R_G = 25\Omega, Starting T_J = 25°C.

100% Eas Test Condition: L = 8mH, I_{AS} = 2A, V_{DD} = 50V, R_G = 25 Ω , Starting T_J = 25°C

- 4. $I_{SD} \le 4A$, dI/dt $\le 200A/\mu s$, $V_{DD} \le BV_{DSS}$, Starting $T_J = 25^{\circ}C$.
- 5. Pulse test: $PW \le 300\mu s$, duty cycle $\le 2\%$.
- 6. For DESIGN AID ONLY, not subject to production testing.
- 7. Switching time is essentially independent of operating temperature.



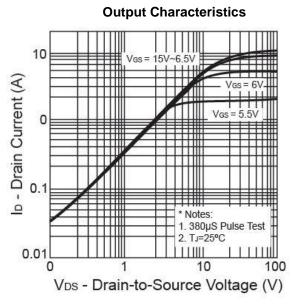
ORDERING INFORMATION

ORDERING CODE	PACKAGE	PACKING
TSM4NB60CI C0G	ITO-220	50pcs / Tube
TSM4NB60CH C5G	TO-251 (IPAK)	75pcs / Tube
TSM4NB60CH X0G	TO-251S (IPAK SL)	75pcs / Tube
TSM4NB60CP ROG	TO-252 (DPAK)	2,500pcs / 13" Reel

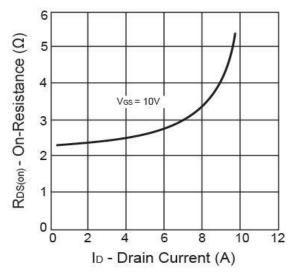


CHARACTERISTICS CURVES

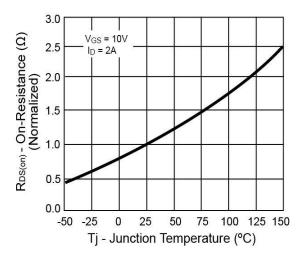
(T_C = 25°C unless otherwise noted)

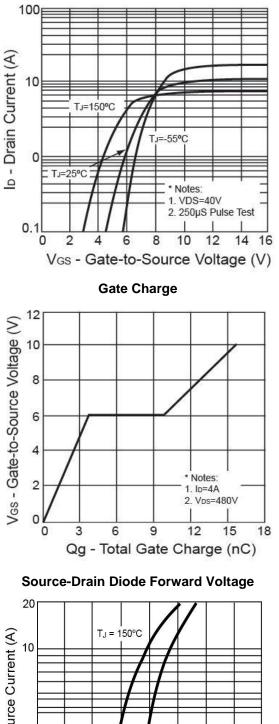


On-Resistance vs. Drain Current

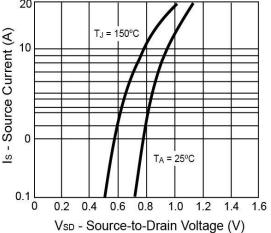


On-Resistance vs. Junction Temperature





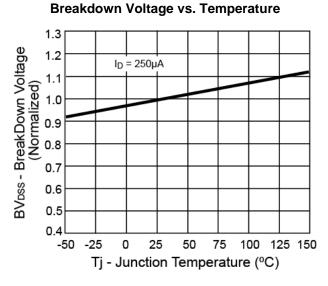
Transfer Characteristics



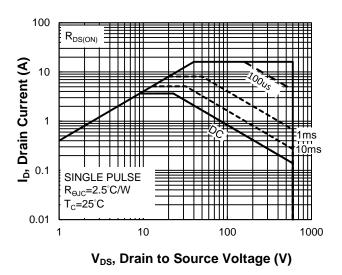


CHARACTERISTICS CURVES

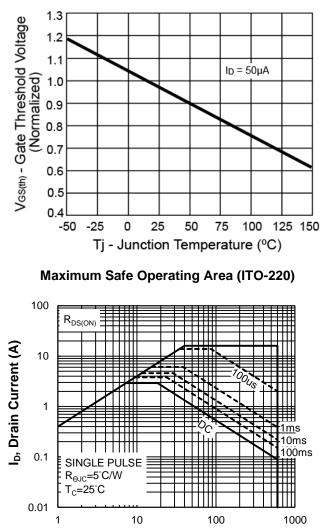
 $(T_C = 25^{\circ}C \text{ unless otherwise noted})$



Maximum Safe Operating Area (IPAK/DPAK)



Threshold Voltage vs. Temperature



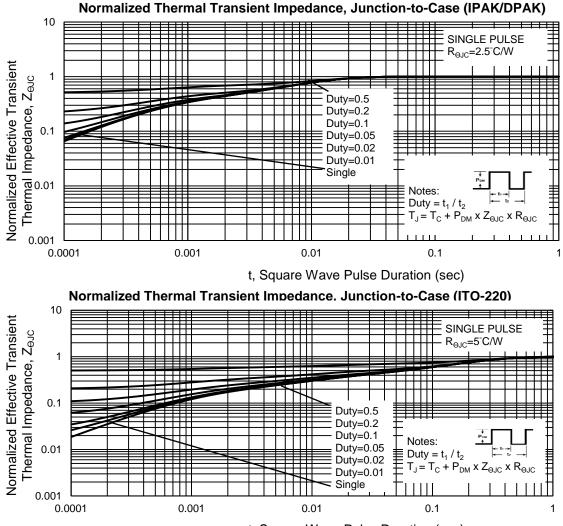
V_{DS}, Drain to Source Voltage (V)





ELECTRICAL CHARACTERISTICS CURVES

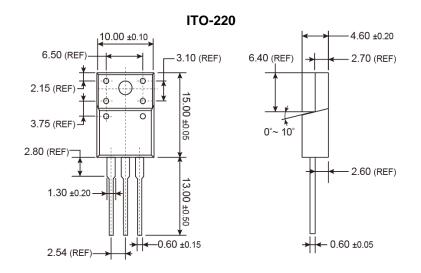
 $(T_c = 25^{\circ}C \text{ unless otherwise noted})$



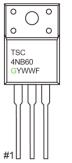
t, Square Wave Pulse Duration (sec)



PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



MARKING DIAGRAM



- **G** = Halogen Free
- Y = Year Code
- WW = Week Code (01~52)
 - **F** = Factory Code

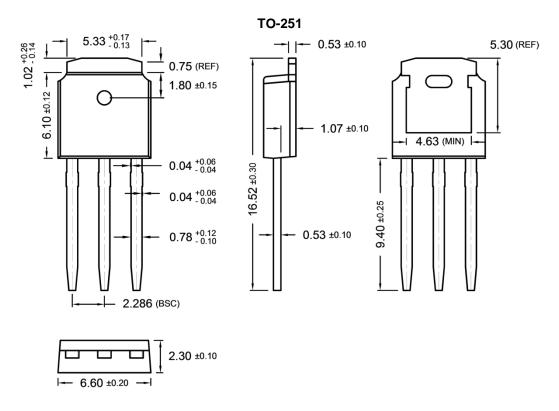
Version: L1901





TAIWAN SEMICONDUCTOR

95



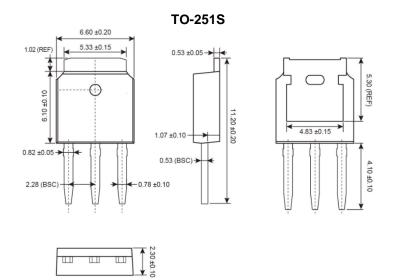
MARKING DIAGRAM

5 0 4NB60	Y = Year CodeM = Month Code for Halogen Free Product
YML CH	O =Jan P =Feb Q =Mar R =Apr
	S =May T =Jun U =Jul V =Aug
	W =Sep X =Oct Y =Nov Z =Dec
	L = Lot Code (1~9, A~Z)

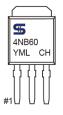




PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



MARKING DIAGRAM



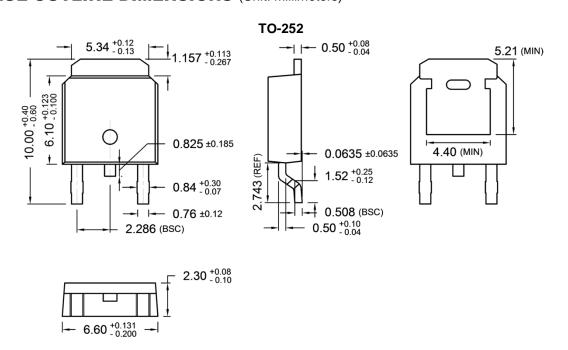
- Y = Year Code
- M = Month Code for Halogen Free Product
- **L** = Lot Code (1~9, A~Z)



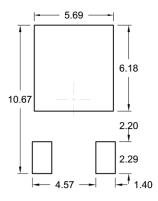


TAIWAN SEMICONDUCTOR

9h



SUGGESTED PAD LAYOUT (Unit: Millimeters)



MARKING DIAGRAM

5	Y = Year CodeM = Month Code for Halogen Free Product	
4NB60 YMLOCP	O =Jan P =Feb Q =Mar R	=Apr
	S =May T =Jun U =Jul V	=Aug
	W =Sep X =Oct Y =Nov Z	=Dec
<i>••</i> 1	L = Lot Code (1~9, A~Z)	



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